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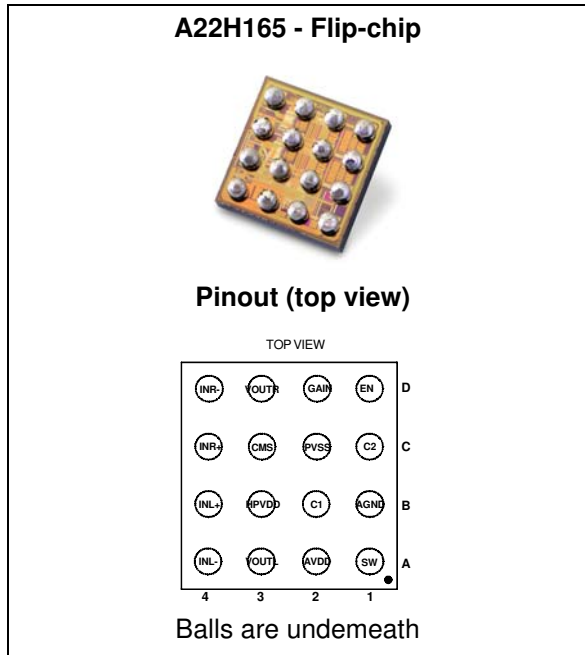
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## High-performance class-G stereo headphone amplifier

Datasheet - production data



- Thermal shutdown
- Flip-chip package: 1.65 mm x 1.65 mm, 400  $\mu\text{m}$  pitch, 16 bumps

### Applications

- Cellular / smart phones
- Portable media player
- Wearable
- Fitness and healthcare

### Description

The A22H165 is a class-G stereo headphone driver dedicated to high-performance audio, high power efficiency and space-constrained applications. It is based on the core technology of a low power dissipation amplifier combined with a high efficiency step-down DC-DC converter for supplying this amplifier. When powered by a battery, the internal step down DC-DC converter generates the appropriate voltage to the amplifier depending on the amplitude of the audio signal to supply the headsets. It achieves a total 2.1 mA current consumption at 100  $\mu\text{W}$  output power (10 dB crest factor). THD+N is 0.02 % maximum at 1 kHz and PSRR is 100 dB at 217 Hz, which ensures a high audio quality of the device in a wide range of environments. The traditionally bulky output coupling capacitors can be removed. A dedicated common-mode sense pin removes parasitic ground noise. The A22H165 is designed to be used with an output serial resistor. It ensures unconditional stability over a wide range of capacitive loads. The A22H165 is packaged in a tiny 16-bump flip-chip package with a pitch of 400  $\mu\text{m}$ .

### Features

- Power supply range: 2.3 V to 4.8 V
- 0.6 mA/channel quiescent current
- 2.1 mA current consumption with 100  $\mu\text{W}$ /channel (10 dB crest factor)
- 0.006% typical THD+N at 1 kHz
- 100 dB typical PSRR at 217 Hz
- 100 dB of SNR A-weighted at G = 0 dB
- Zero "pop and click"
- Gain settings: 0 dB and 6 dB
- Integrated high efficiency step-down converter
- Low standby current: 5  $\mu\text{A}$  max
- Output-coupling capacitors removed

Table 1. Device summary

Order code	Temperature range	Package	Packing	Marking
A22H165	-40°C to +85°C	Flip-chip	Tape & reel	21

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# 1 Absolute maximum ratings and operating conditions

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply voltage <sup>(1)</sup> during 1 ms.	5.5	V
$V_{in+}, V_{in-}$	Input voltage referred to ground	+/- 1.2	V
Control input voltage	EN, Gain	-0.3 to VDD	V
$T_{stg}$	Storage temperature	-65 to +150	°C
$T_j$	Maximum junction temperature <sup>(2)</sup>	150	°C
$R_{thja}$	Thermal resistance junction to ambient <sup>(3)</sup>	200	°C/W
$P_d$	Power dissipation	Internally limited <sup>(4)</sup>	
ESD	Human body model (HBM) <sup>(5)</sup> All pins VOUTR, VOUTL vs. AGND	2 4	kV
	Machine model (MM), min. value <sup>(6)</sup>	100	V
	Charge device model (CDM) All pins VOUTR, VOUTL	500 750	V
	IEC61000-4-2 level 4, contact <sup>(7)</sup> IEC61000-4-2 level 4, air discharge <sup>(7)</sup>	+/- 8 +/- 15	kV
	Lead temperature (soldering, 10 sec)	260	°C

1. All voltage values are measured with respect to the ground pin.
2. Thermal shutdown is activated when maximum junction temperature is reached.
3. The device is protected from over temperature by a thermal shutdown mechanism, active at 150° C.
4. Exceeding the power derating curves for long periods may provoke abnormal operation.
5. Human body model: a 100 pF capacitor is charged to the specified voltage, then discharged through a 1.5 kΩ resistor between two pins of the device. This is done for all couples of connected pin combinations while the other pins are floating.
6. Machine model: a 200 pF capacitor is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω). This is done for all couples of connected pin combinations while the other pins are floating.
7. The measurement is performed on an evaluation board, with ESD protection EMIF02-AV01F3.

Table 3. Operating conditions

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply voltage	2.3 to 4.8	V
HPVDD	internal step-down DC output voltages High rail voltage Low rail voltage	1.9 1.2	V
EN,GAIN	Input voltage low level	0.6 V max	V
EN,GAIN	Input voltage high level	1.3 V min	
$R_L$	Load resistor	$\geq 16$	$\Omega$
$C_L$	Load capacitor Serial resistor of 12 $\Omega$ minimum, $R_L \geq 16 \Omega$	0.8 to 100	nF
$T_{oper}$	Operating free air temperature range	-40 to +85	$^{\circ}\text{C}$
$R_{thja}$	Flip-chip thermal resistance junction to ambient	90	$^{\circ}\text{C/W}$

## 2 Typical application schematic

Figure 1. Typical application schematic for the A22H165

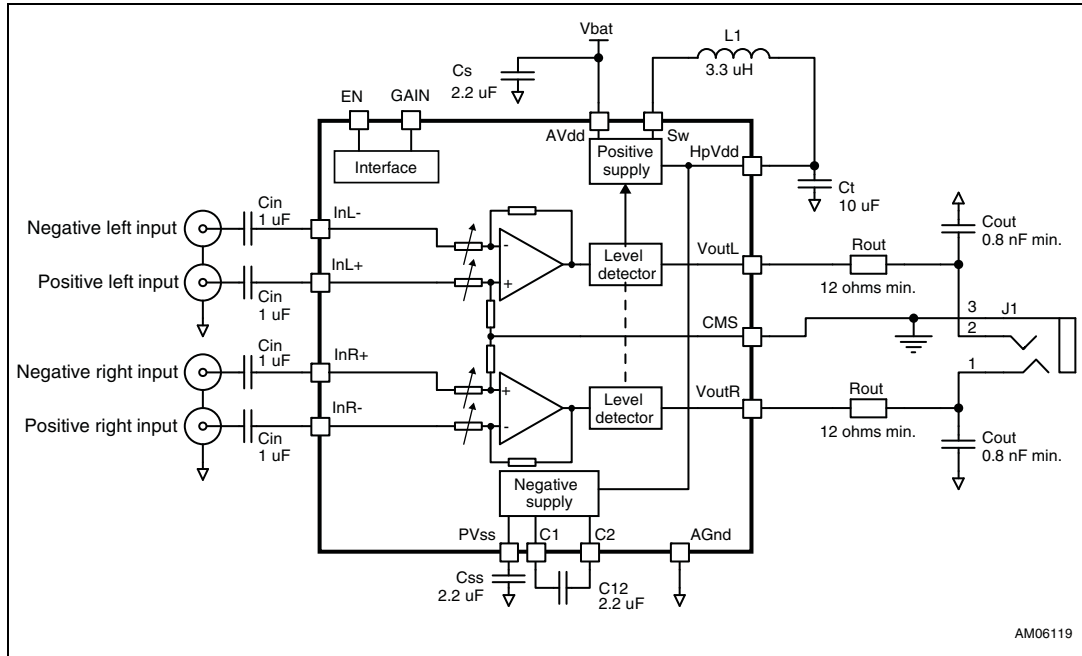


Table 4. A22H165 pin description

Pin n°	Pin name	Pin definition
A1	SW	Switching node of the buck converter
A2	AVDD	Analog supply voltage, connect to battery
A3	VOUTL	Output signal for left audio channel
A4	INL-	Negative input signal for left audio channel
B1	AGND	Device ground
B2	C1	Flying capacitor terminal for internal negative supply generator
B3	HPVDD	Buck converter output, power supply for amplifier
B4	INL+	Positive input signal for left audio channel
C1	C2	Flying capacitor terminal for internal negative supply generator
C2	PVSS	Negative supply generator output
C3	CMS	Common-mode sense, to be connected as close as possible to the ground of headphone/line out plug
C4	INR+	Positive input signal for right audio channel
D1	EN	Amplifier enable
D2	GAIN	Amplifier gain select
D3	VOUTr	Output signal for right audio channel
D4	INR-	Negative input signal for right audio channel

**Table 5. A22H165 component description**

Component <sup>(1)</sup>	Value	Description
C <sub>s</sub>	2.2 μF	Decoupling capacitors for V <sub>CC</sub> . A 2.2 μF capacitor is sufficient for proper decoupling of the A22H165. An X5R dielectric and 10 V rating voltage is recommended to minimize ΔC/ΔV when V <sub>CC</sub> = 4.8 V. Must be placed as close as possible to the A22H165 to minimize parasitic inductance and resistance.
C12	2.2 μF	Capacitor for internal negative power supply operation. An X5R dielectric and 6.3 V rating voltage is recommended to minimize ΔC/ΔV when HPVDD = 1.9 V. Must be placed as close as possible to the A22H165 to minimize parasitic inductance and resistance.
C <sub>SS</sub>	2.2 μF	Filtering capacitor for internal negative power supply. An X5R dielectric and 6.3 V rating voltage is recommended to minimize ΔC/ΔV when HPVDD = 1.9 V.
C <sub>in</sub>	$C_{in} = \frac{1}{2 \times \pi \times R_{in} \times F_c}$	Input coupling capacitor that forms with R <sub>in</sub> ≈ R <sub>indiff</sub> /2 a first-order high-pass filter with a -3 dB cut-off frequency F <sub>c</sub> .
C <sub>out</sub>	0.8 to 100 nF	Output capacitor of 0.8 nF minimum to 100 nF maximum. This capacitor is mandatory for operation of the A22H165.
R <sub>out</sub>	12 Ω min.	Output resistor in-series with the A22H165 output. This 12 Ω minimum resistor is mandatory for operation of the A22H165.
L1	3.3 μH	Inductor for internal DC-DC step-down converter. References of inductors: refer to <a href="#">Section 4.3.1</a> for more information.
C <sub>t</sub>	10 μF	Tank capacitor for internal DC-DC step-down converter. An X5R dielectric and 6.3 V rating voltage is recommended to minimize ΔC/ΔV when HPVDD = 1.9 V. Refer to <a href="#">Section 4.3.2</a> for more information.

1. Refer to [Section 4.3](#) for a complete description of each component.

### 3 Electrical characteristics

The values given in the following table are for the conditions  $V_{CC} = +3.6\text{ V}$ ,  $AGND = 0\text{ V}$ ,  $GAIN = 0\text{ dB}$ ,  $R_L = 32\ \Omega + 15\ \Omega$ ,  $T_{amb} = 25^\circ\text{ C}$ , unless otherwise specified.

**Table 6. Electrical characteristics of the amplifier**

Symbol	Parameter	Min.	Typ.	Max.	Unit
$I_{CC}$	Quiescent supply current, no input signal, both channels enabled		1.2	1.5	mA
$I_s$	Supply current, with input modulation, both channels enabled, $HPVDD = 1.2\text{ V}$ , output power per channel, $F = 1\text{ kHz}$ $P_{out} = 100\ \mu\text{W}$ at 3 dB crest factor $P_{out} = 500\ \mu\text{W}$ at 3 dB crest factor $P_{out} = 1\text{ mW}$ at 3 dB crest factor $P_{out} = 100\ \mu\text{W}$ at 10 dB crest factor $P_{out} = 500\ \mu\text{W}$ at 10 dB crest factor $P_{out} = 1\text{ mW}$ at 10 dB crest factor		2.3 3.7 4.7 2.1 3.1 3.9	3.5 5 6.5	mA
$I_{STBY}$	Standby current, no input signal, $V_{EN} = 0\text{ V}$ , $V_{GAIN}=0\text{V}$		0.6	5	$\mu\text{A}$
$V_{in}$	Input differential voltage range <sup>(1)</sup>			1	$V_{rms}$
$V_{oo}$	Output offset voltage No input signal	-500		+500	$\mu\text{V}$
$V_{out}$	Maximum output voltage, in-phase signals $R_L = 16\ \Omega$ , $THD+N = 1\%$ max, $f = 1\text{ kHz}$ $R_L = 47\ \Omega$ , $THD+N = 1\%$ max, $f = 1\text{ kHz}$ $R_L = 10\text{ k}\Omega$ , $P_s = 15\ \Omega$ , $C_L = 1\text{ nF}$ , $THD+N = 1\%$ max, $f = 1\text{ kHz}$	0.6 1.0 1.0	0.8 1.1 1.3		$V_{rms}$
THD+N	Total harmonic distortion + noise, $G = 0\text{ dB}$ $V_{out} = 700\text{ mV}_{rms}$ , $F = 1\text{ kHz}$ $V_{out} = 700\text{ mV}_{rms}$ , $20\text{ Hz} < F < 20\text{ kHz}$		0.006 0.05	0.02	%
PSRR	Power supply rejection ratio <sup>(1)</sup> , $V_{ripple} = 200\text{ mV}_{pp}$ , grounded inputs $F = 217\text{ Hz}$ , $G = 0\text{ dB}$ , $R_L \geq 16\ \Omega$ $F = 10\text{ kHz}$ , $G = 0\text{ dB}$ , $R_L \geq 16\ \Omega$	90	100 70		dB
CMRR	Common mode rejection ratio $F = 1\text{ kHz}$ , $G = 0\text{ dB}$ , $V_{ic} = 200\text{ mV}_{pp}$ $F = 20\text{ Hz to } 20\text{ kHz}$ , $G = 0\text{ dB}$ , $V_{ic} = 200\text{ mV}_{pp}$		65 45		dB
Crosstalk	Channel separation $R_L = 32\ \Omega + 15\ \Omega$ , $G = 0\text{ dB}$ , $F = 1\text{ kHz}$ , $P_o = 10\text{ mW}$	60	100		dB
SNR	Signal-to-noise ratio, A-weighted, $V_{out} = 1\text{ V}_{rms}$ , $THD+N < 1\%$ , $F = 1\text{ kHz}$ <sup>(1)</sup> $G = +0\text{ dB}$	100			dB
ONoise	Output noise voltage, A-weighted <sup>(1)</sup> $G = +0\text{ dB}$			9	$\mu\text{V}_{rms}$



Table 6. Electrical characteristics of the amplifier (continued)

Symbol	Parameter	Min.	Typ.	Max.	Unit
AV	Closed loop voltage gain, GAIN=L		0		dB
	Closed loop voltage gain, GAIN=H		6		dB
DAV	Gain matching between left and right channels	-0.5		+0.5	dB
R <sub>indiff</sub>	Differential input impedance at 6 dB	24	33.2		kΩ
V <sub>IL</sub>	Low level input voltage on EN, GAIN pins			0.6	V
V <sub>IH</sub>	High level input voltage on EN, GAIN pins	1.3			V
I <sub>in</sub>	Input current on EN,GAIN			10	μA

1. Guaranteed by design and parameter correlation.

Figure 2. Current consumption vs. power supply voltage



Figure 3. Standby current consumption vs. power supply voltage

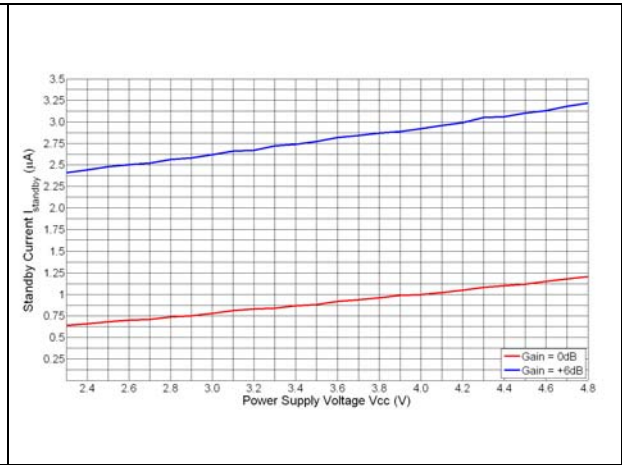


Figure 4. Maximum output power vs. power supply voltage, R<sub>L</sub> = 16 Ω

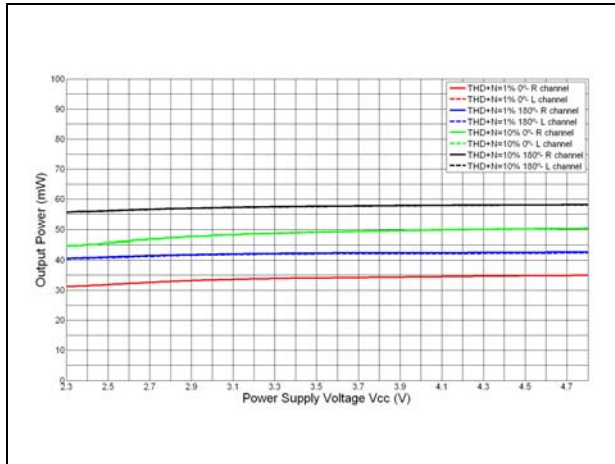


Figure 5. Maximum output power vs. power supply voltage, R<sub>L</sub> = 32 Ω

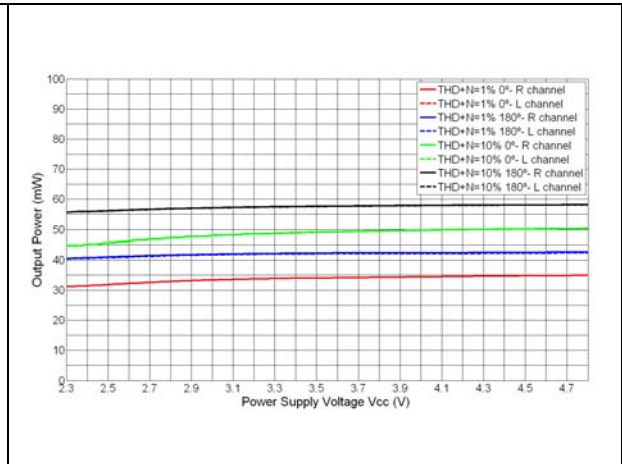


Figure 6. Maximum output power vs. power supply voltage, R<sub>L</sub> = 47 Ω

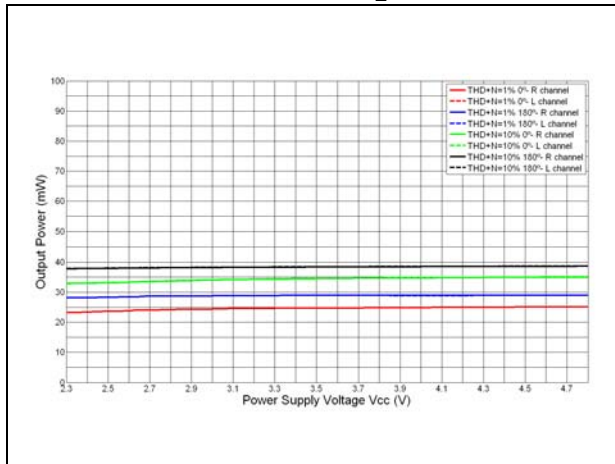


Figure 7. Current consumption vs. total output power, R<sub>L</sub> = 16 Ω

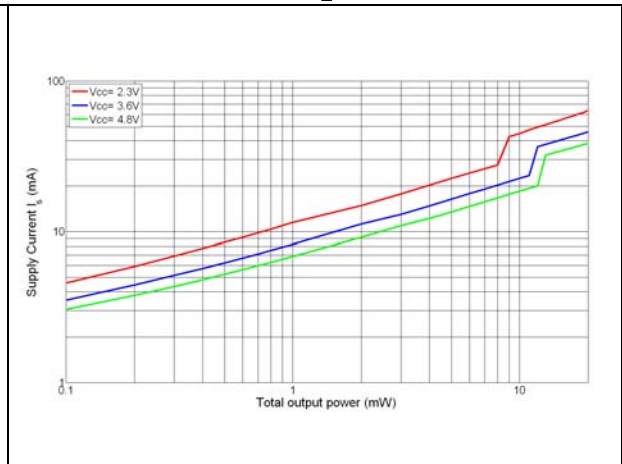


Figure 8. Current consumption vs. total output power,  $R_L = 32 \Omega$

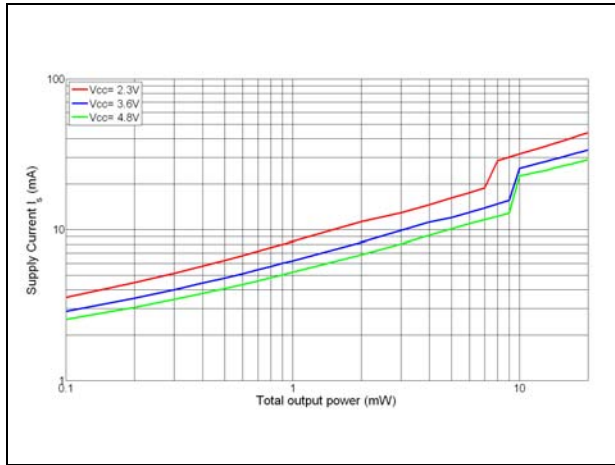


Figure 9. Current consumption vs. total output power,  $R_L = 47 \Omega$

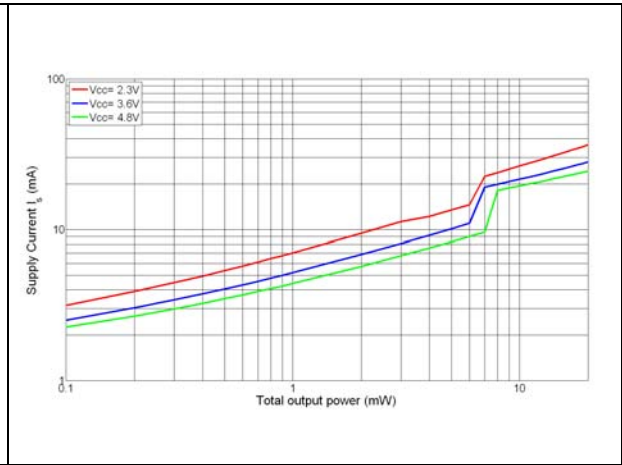


Figure 10. Differential input impedance vs. gain

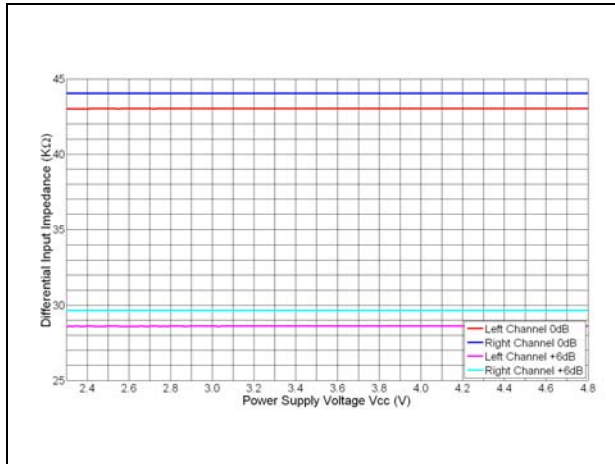


Figure 11. THD+N vs. output power -  $R_L = 16 \Omega$ , in-phase,  $V_{CC} = 2.5 V$

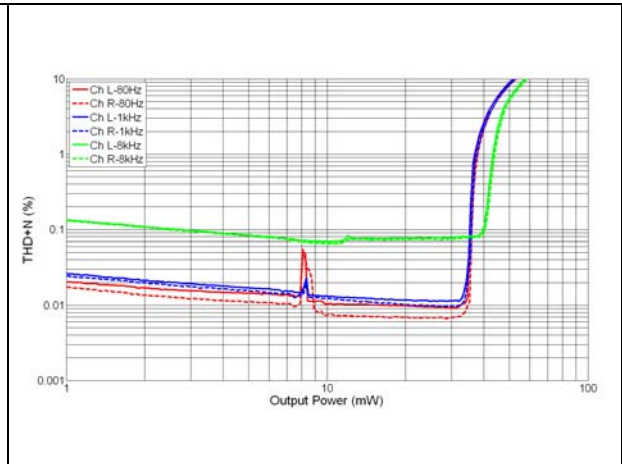


Figure 12. THD+N vs. output power -  $R_L = 16 \Omega$ , out-of-phase,  $V_{CC} = 2.5 V$

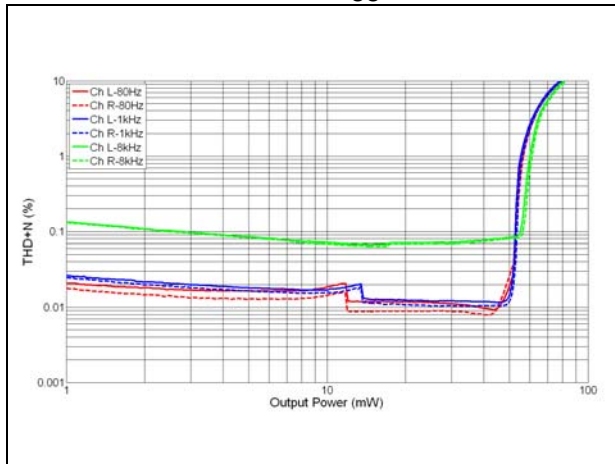


Figure 13. THD+N vs. output power -  $R_L = 16 \Omega$ , in-phase,  $V_{CC} = 3.6 V$

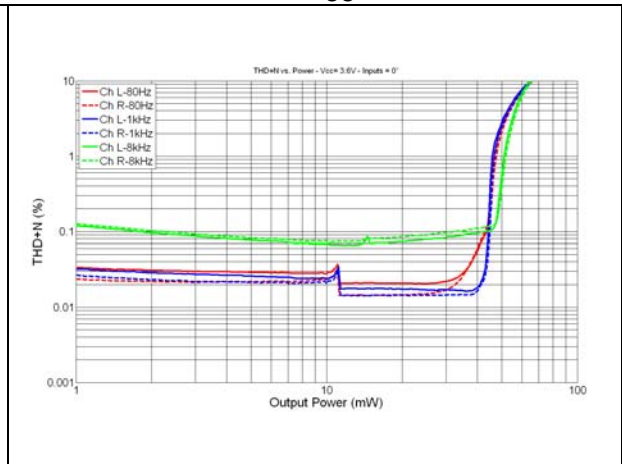


Figure 14. THD+N vs. output power -  $R_L = 16 \Omega$ , out-of-phase,  $V_{CC} = 3.6 V$

Figure 15. THD+N vs. output power -  $R_L = 16 \Omega$ , in-phase,  $V_{CC} = 4.8 V$

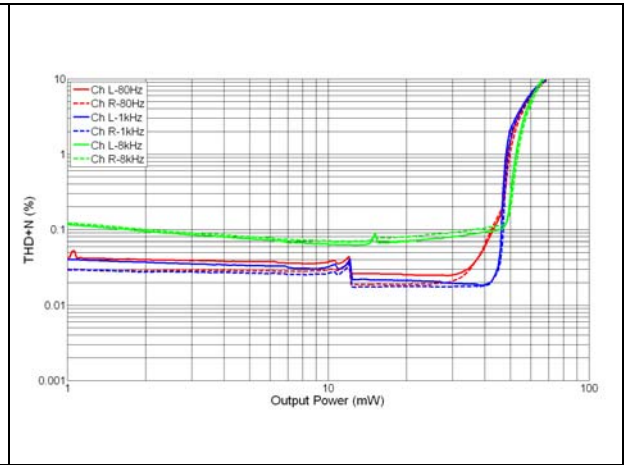
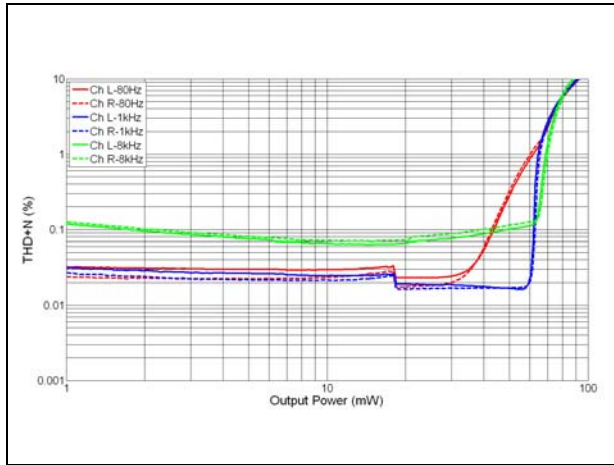


Figure 16. THD+N vs. output power -  $R_L = 16 \Omega$ , out-of-phase,  $V_{CC} = 4.8 V$

Figure 17. THD+N vs. output power -  $R_L = 32 \Omega$ , in-phase,  $V_{CC} = 2.5 V$

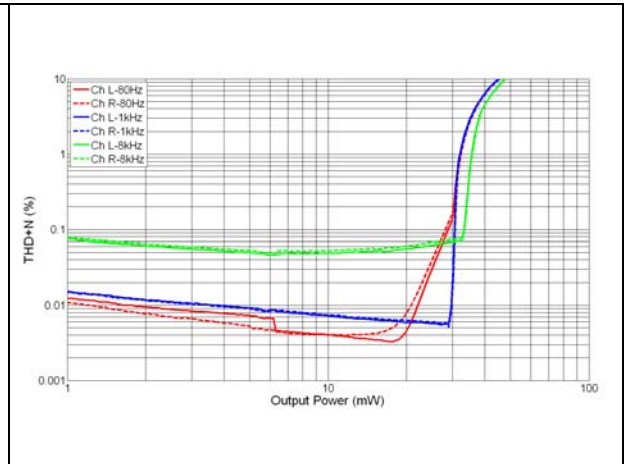
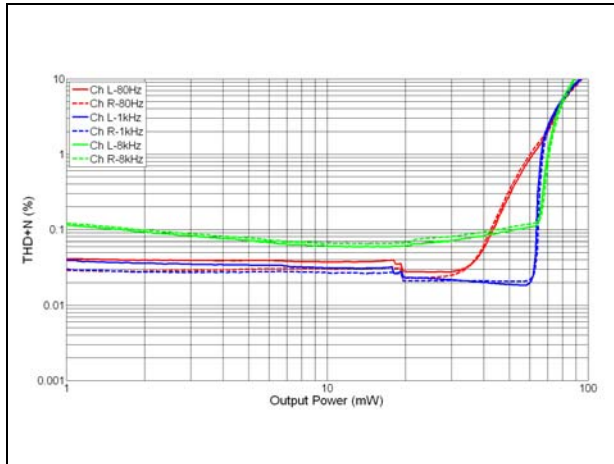


Figure 18. THD+N vs. output power -  $R_L = 32 \Omega$ , out-of-phase,  $V_{CC} = 2.5 V$

Figure 19. THD+N vs. output power -  $R_L = 32 \Omega$ , in-phase,  $V_{CC} = 3.6 V$

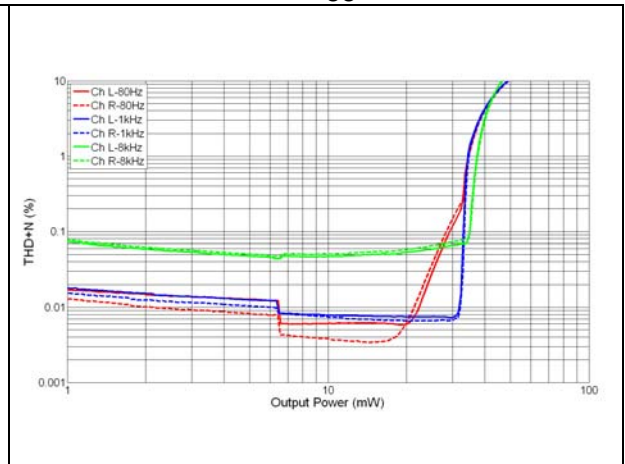
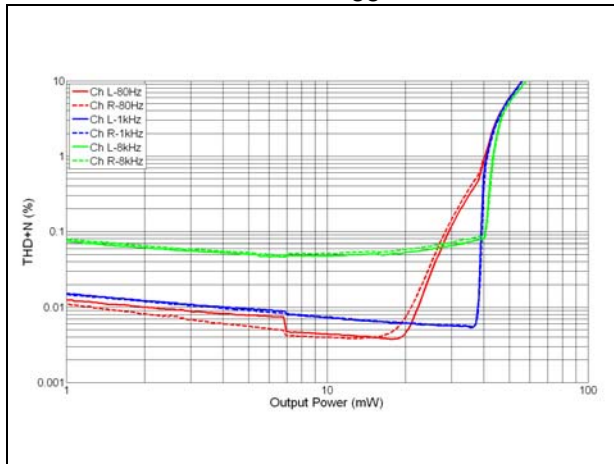


Figure 20. THD+N vs. output power -  $R_L = 32 \Omega$ , out-of-phase,  $V_{CC} = 3.6 V$

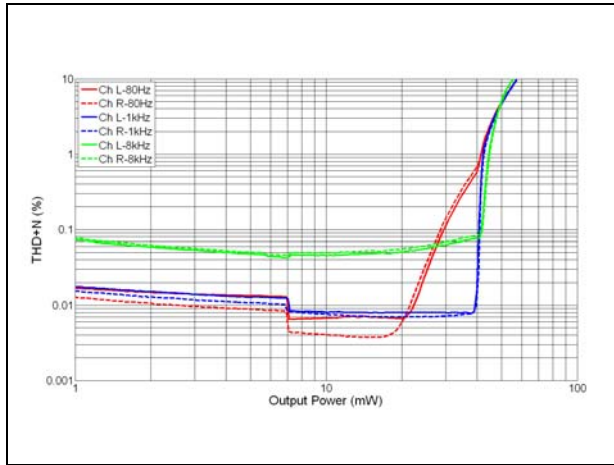


Figure 21. THD+N vs. output power -  $R_L = 32 \Omega$ , in-phase,  $V_{CC} = 4.8 V$

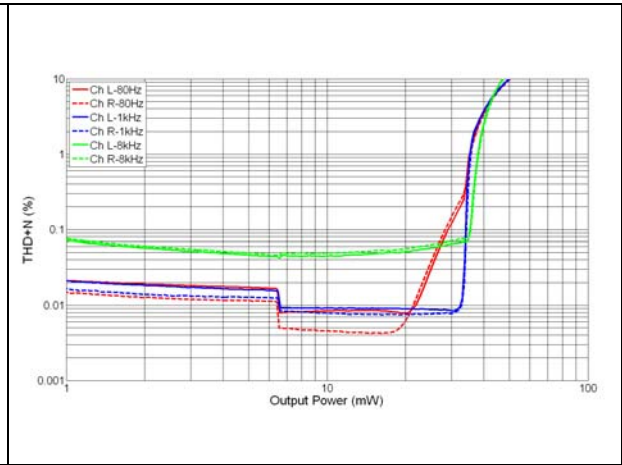


Figure 22. THD+N vs. output power -  $R_L = 32 \Omega$ , out-of-phase,  $V_{CC} = 4.8 V$

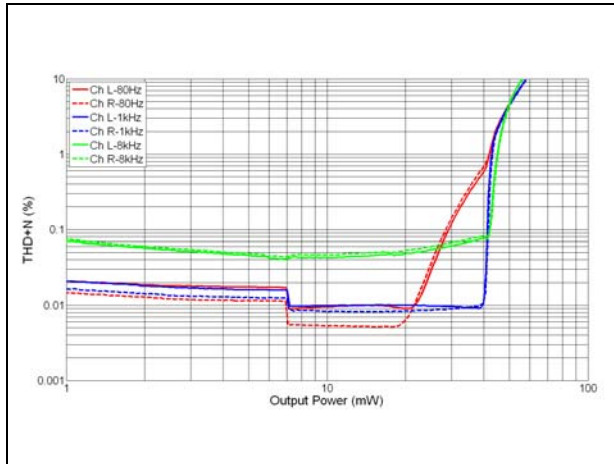


Figure 23. THD+N vs. output power -  $R_L = 32 \Omega$ , +IPad, in-phase,  $V_{CC} = 2.5 V$

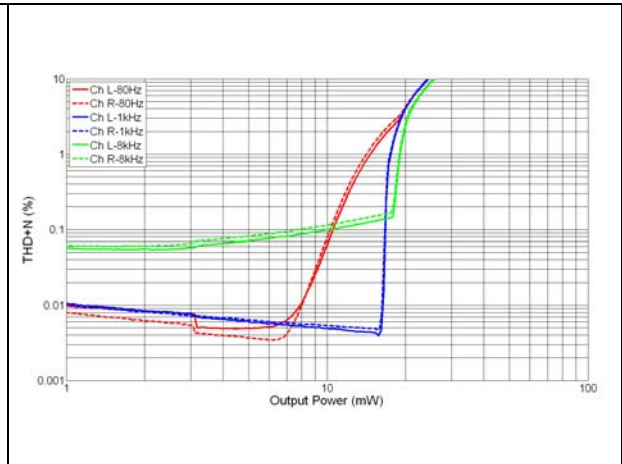


Figure 24. THD+N vs. output power -  $R_L = 32 \Omega$ , +IPad, out-of-phase,  $V_{CC} = 2.5 V$

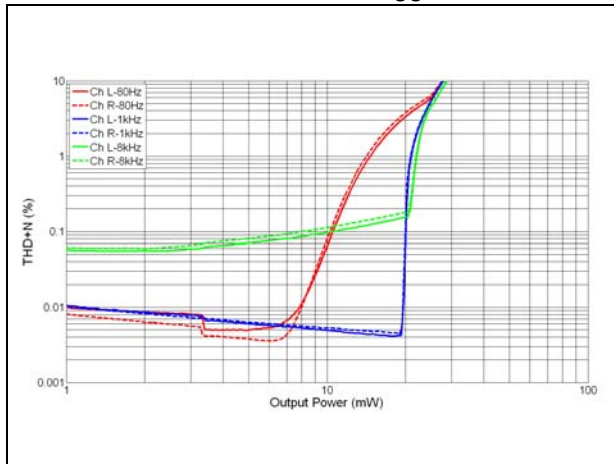


Figure 25. THD+N vs. output power -  $R_L = 32 \Omega$ , +IPad, in-phase,  $V_{CC} = 3.6 V$

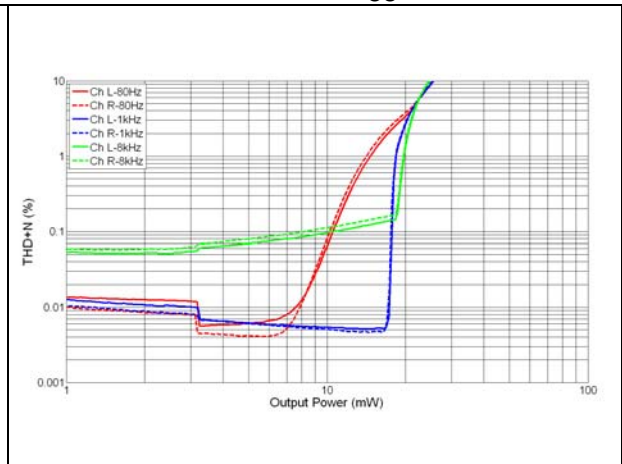




Figure 26. THD+N vs. output power -  $R_L = 32 \Omega$  +IPad, out-of-phase,  $V_{CC} = 3.6 V$

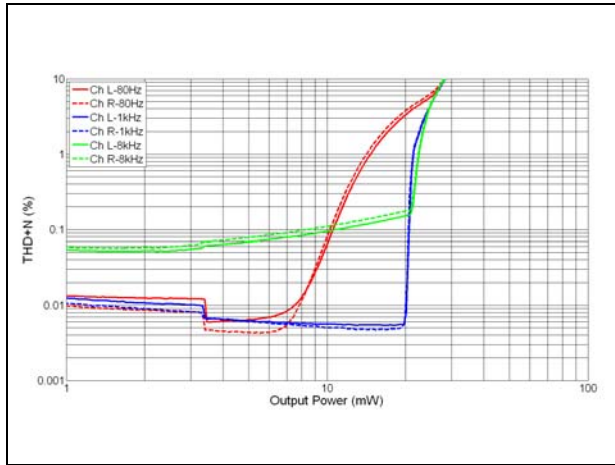


Figure 27. THD+N vs. output power -  $R_L = 32 \Omega$  +IPad, in-phase,  $V_{CC} = 4.8 V$

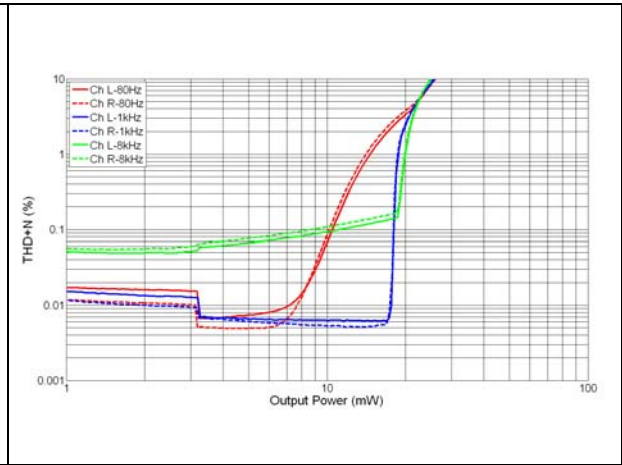


Figure 28. THD+N vs. output power -  $R_L = 32 \Omega$  +IPad, out-of-phase,  $V_{CC} = 4.8 V$

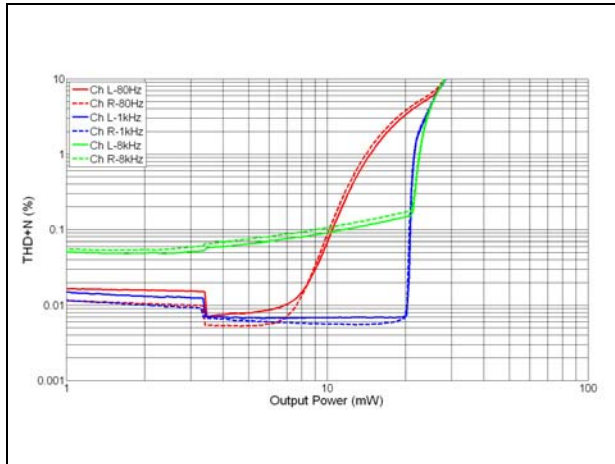


Figure 29. THD+N vs. output power -  $R_L = 47 \Omega$ , in-phase,  $V_{CC} = 2.5 V$

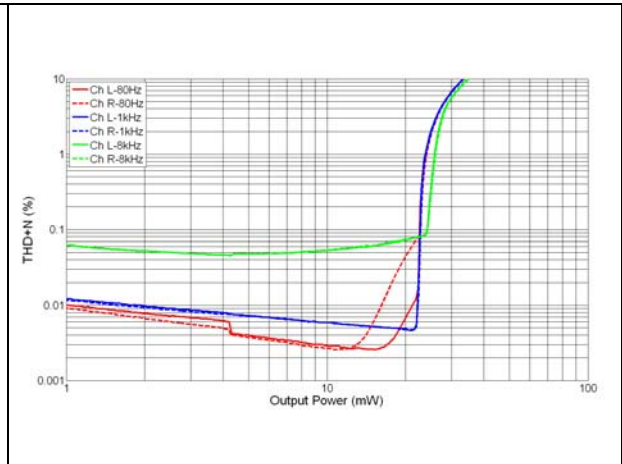


Figure 30. THD+N vs. output power -  $R_L = 47 \Omega$ , out-of-phase,  $V_{CC} = 2.5 V$

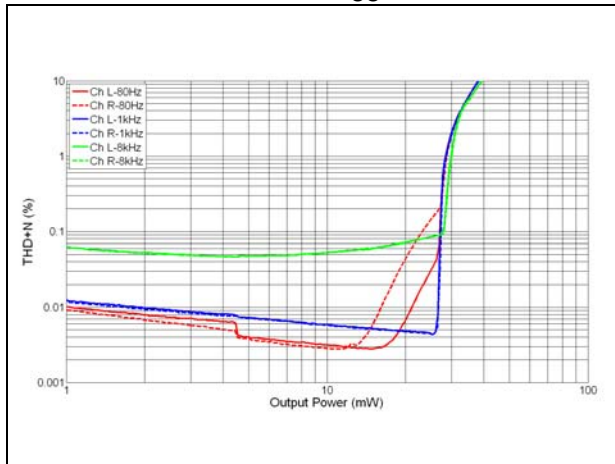


Figure 31. THD+N vs. output power -  $R_L = 47 \Omega$ , in-phase,  $V_{CC} = 3.6 V$

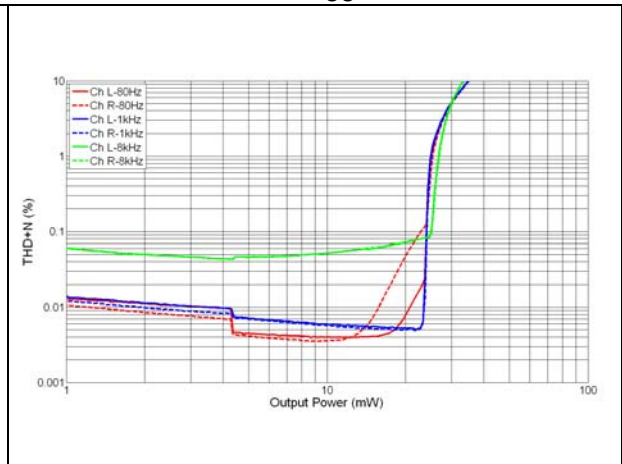




Figure 32. THD+N vs. output power -  $R_L = 47 \Omega$ , out-of-phase,  $V_{CC} = 3.6 V$

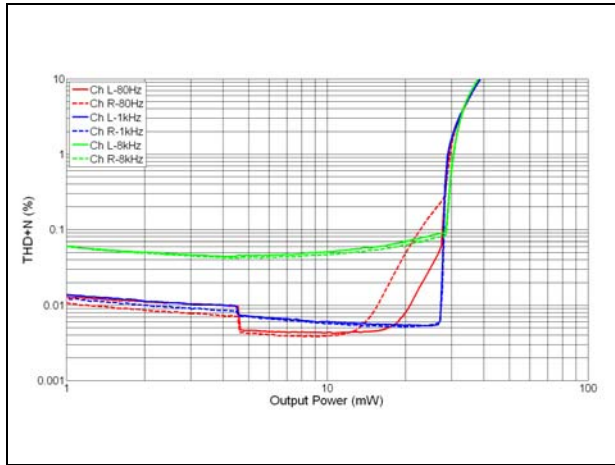


Figure 33. THD+N vs. output power -  $R_L = 47 \Omega$ , in-phase,  $V_{CC} = 4.8 V$

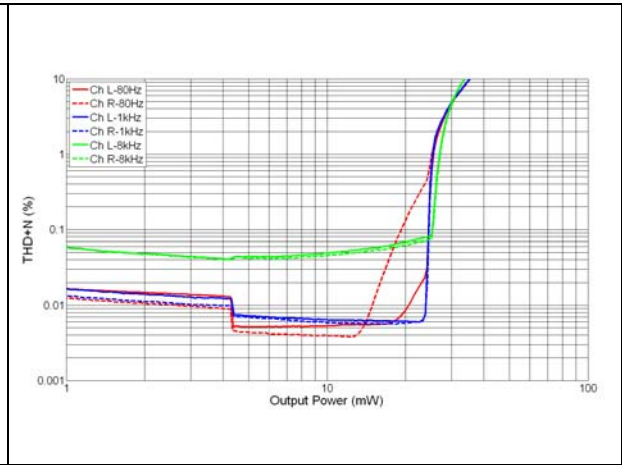


Figure 34. THD+N vs. output power -  $R_L = 47 \Omega$ , out-of-phase,  $V_{CC} = 4.8 V$

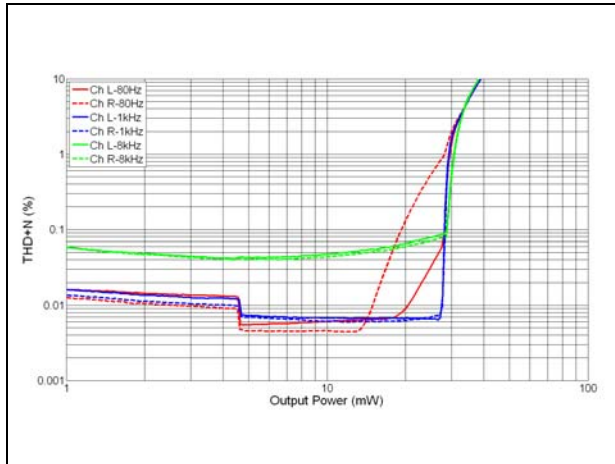


Figure 35. THD+N vs. frequency,  $R_L = 16 \Omega$ , in-phase,  $V_{CC} = 2.5 V$

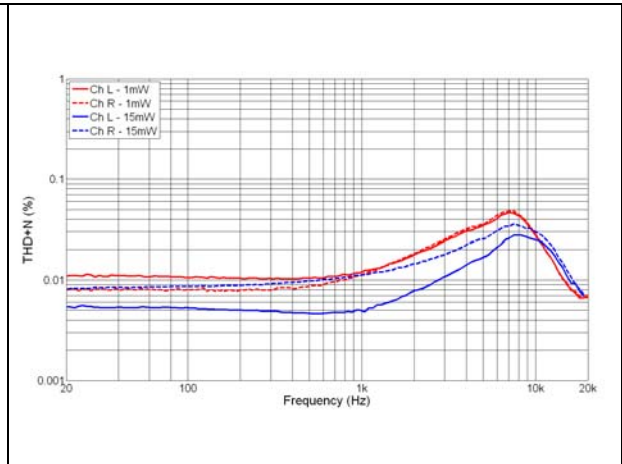


Figure 36. THD+N vs. frequency,  $R_L = 16 \Omega$ , out-of-phase,  $V_{CC} = 2.5 V$

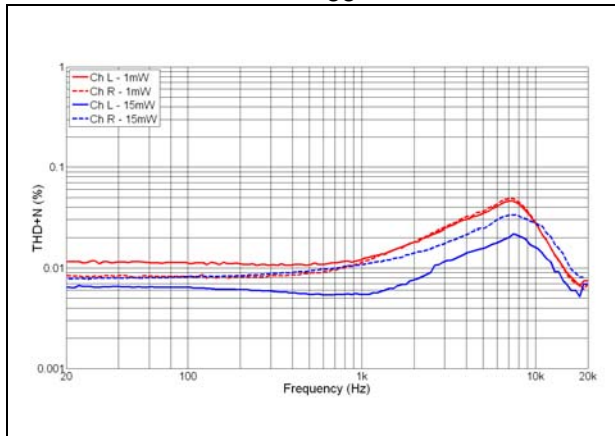


Figure 37. THD+N vs. frequency,  $R_L = 16 \Omega$ , in-phase,  $V_{CC} = 3.6 V$

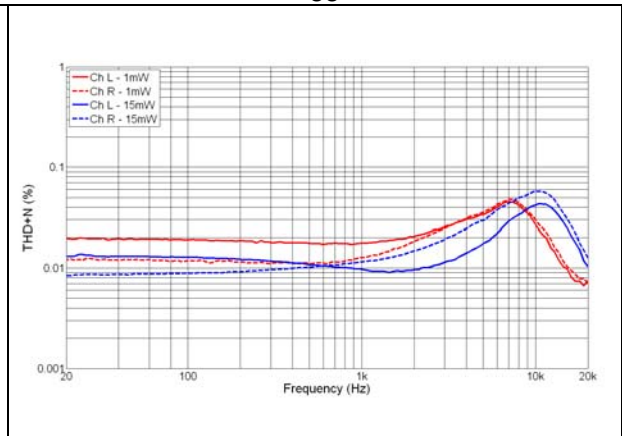


Figure 38. THD+N vs. frequency,  $R_L = 16 \Omega$ , out-of-phase,  $V_{CC} = 3.6 V$

Figure 39. THD+N vs. frequency,  $R_L = 16 \Omega$ , in-phase,  $V_{CC} = 4.8 V$

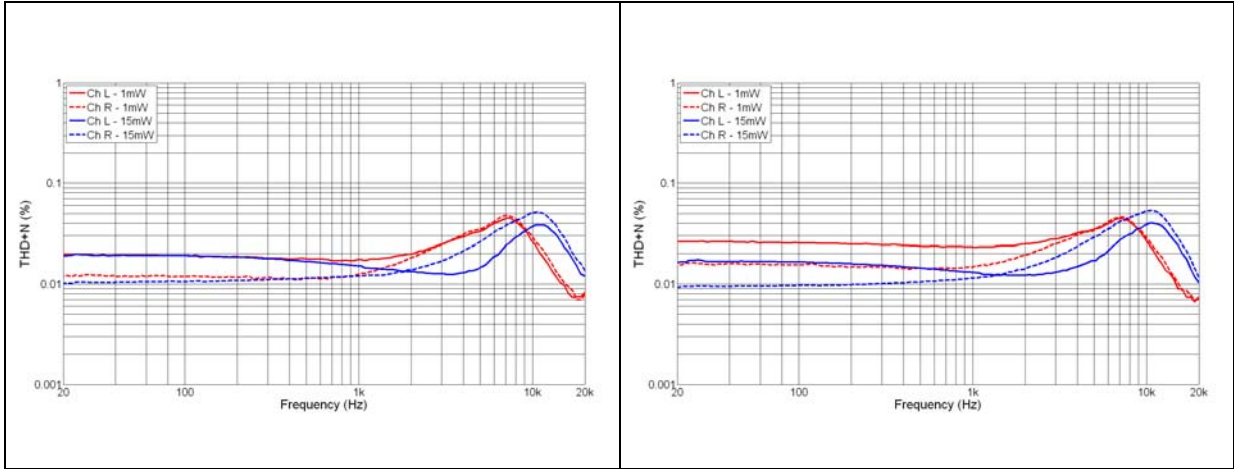


Figure 40. THD+N vs. frequency,  $R_L = 16 \Omega$ , out-of-phase,  $V_{CC} = 4.8 V$

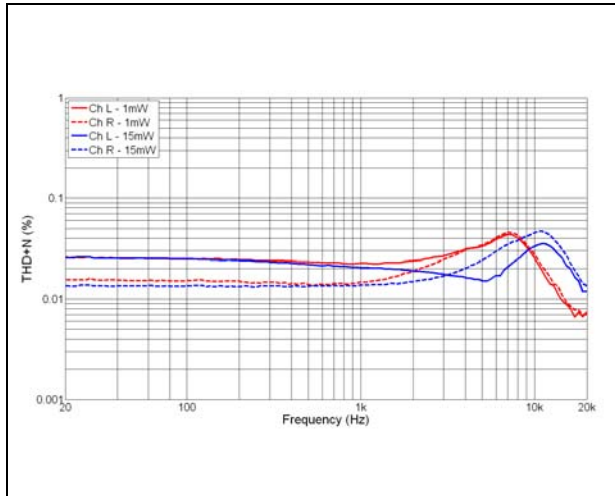


Figure 41. THD+N vs. frequency,  $R_L = 32 \Omega$ , in-phase,  $V_{CC} = 2.5 V$

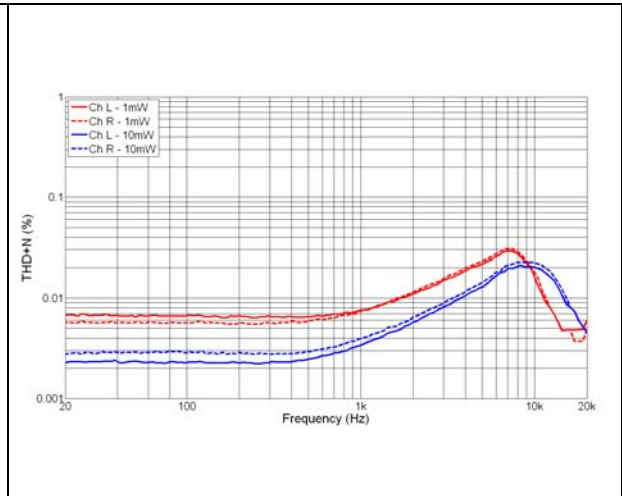


Figure 42. THD+N vs. frequency,  $R_L = 32 \Omega$ , out-of-phase,  $V_{CC} = 2.5 V$

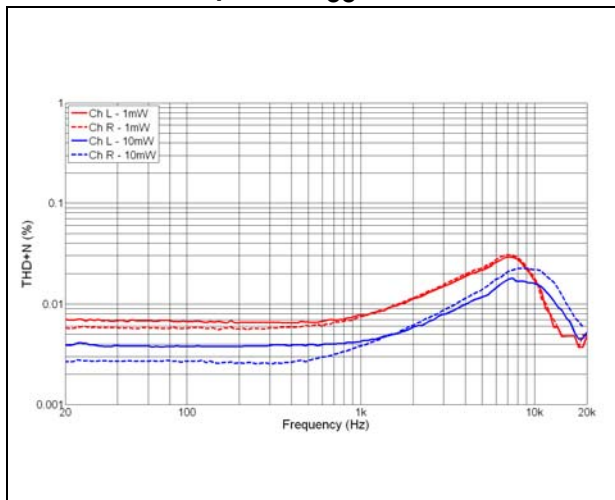


Figure 43. THD+N vs. frequency,  $R_L = 32 \Omega$ , in-phase,  $V_{CC} = 3.6 V$

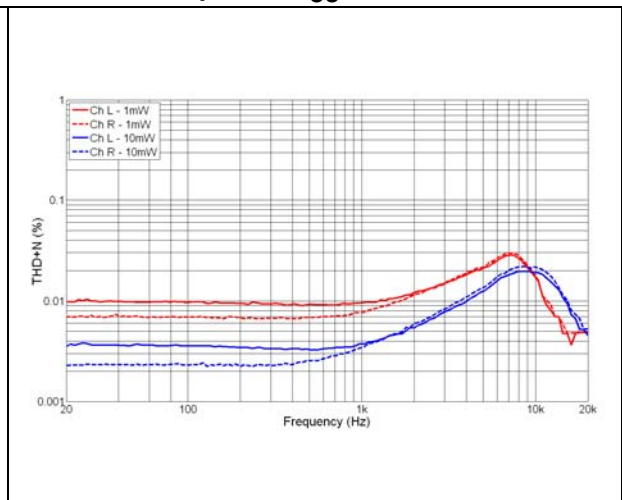


Figure 44. THD+N vs. frequency,  $R_L = 32 \Omega$ , out-of-phase,  $V_{CC} = 3.6 V$

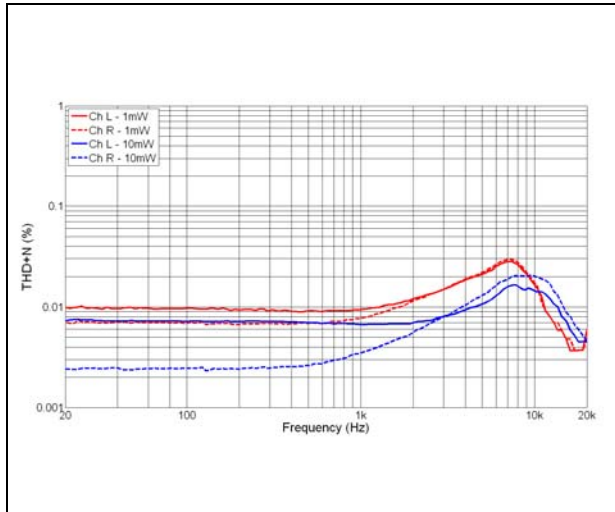


Figure 45. THD+N vs. frequency,  $R_L = 32 \Omega$ , in-phase,  $V_{CC} = 4.8 V$

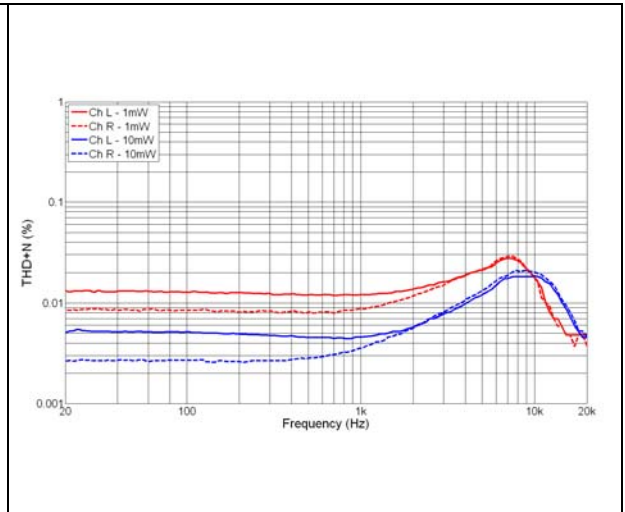


Figure 46. THD+N vs. frequency,  $R_L = 32 \Omega$ , out-of-phase,  $V_{CC} = 4.8 V$

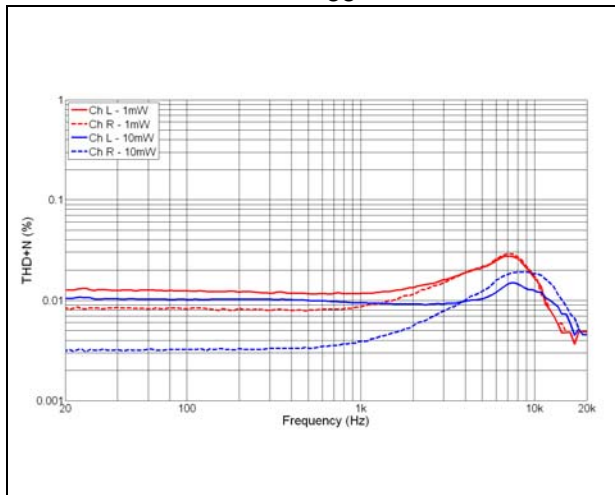


Figure 47. THD+N vs. frequency,  $R_L = 47 \Omega$ , in-phase,  $V_{CC} = 2.5 V$

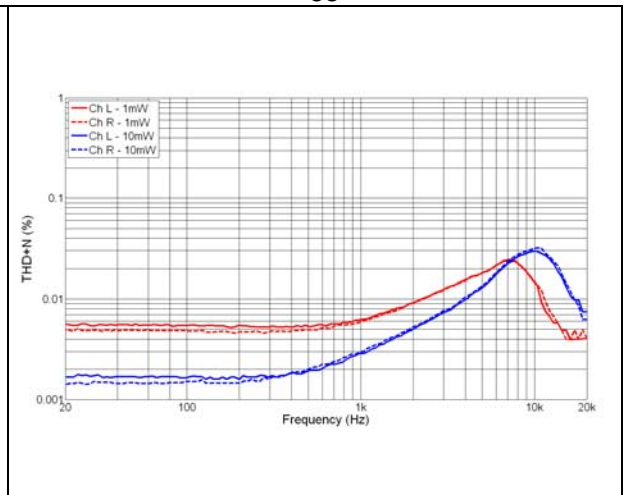


Figure 48. THD+N vs. frequency,  $R_L = 47 \Omega$ , out-of-phase,  $V_{CC} = 2.5 V$

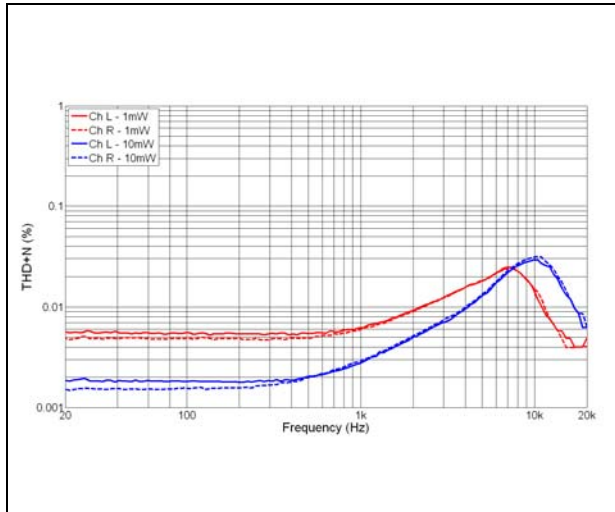


Figure 49. THD+N vs. frequency,  $R_L = 47 \Omega$ , in-phase,  $V_{CC} = 3.6 V$

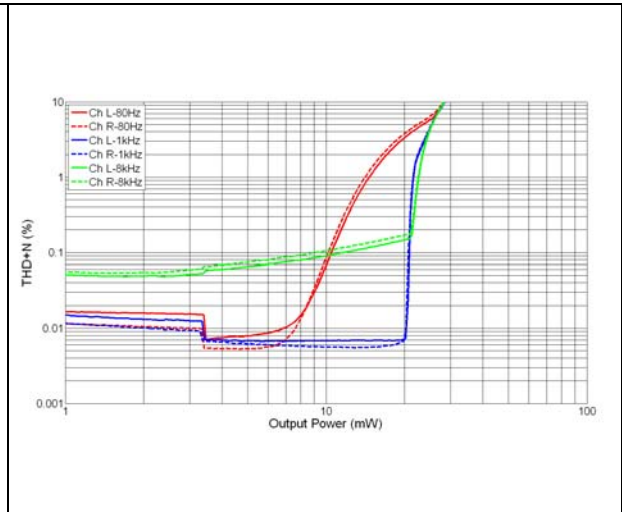


Figure 50. THD+N vs. frequency,  $R_L = 47 \Omega$ , out-of-phase,  $V_{CC} = 3.6 V$

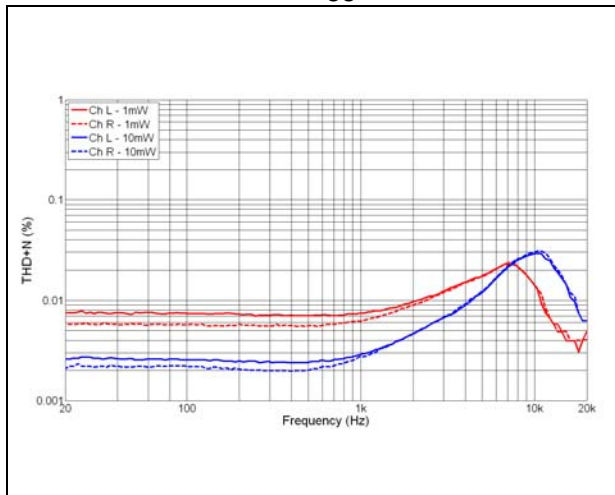


Figure 51. THD+N vs. frequency,  $R_L = 47 \Omega$ , in-phase,  $V_{CC} = 4.8 V$

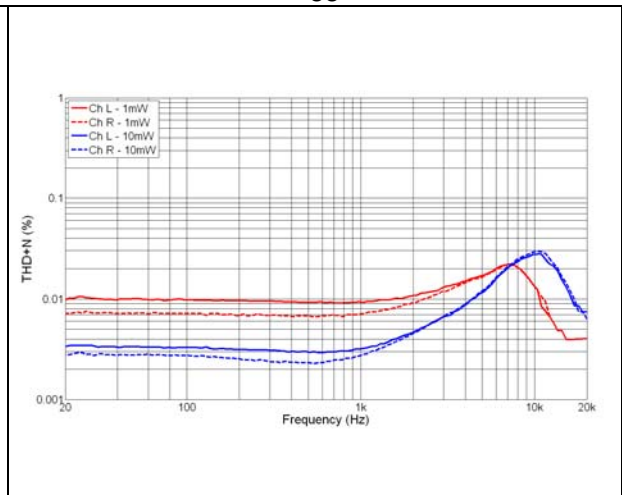


Figure 52. THD+N vs. frequency,  $R_L = 47 \Omega$ , out-of-phase,  $V_{CC} = 4.8 V$

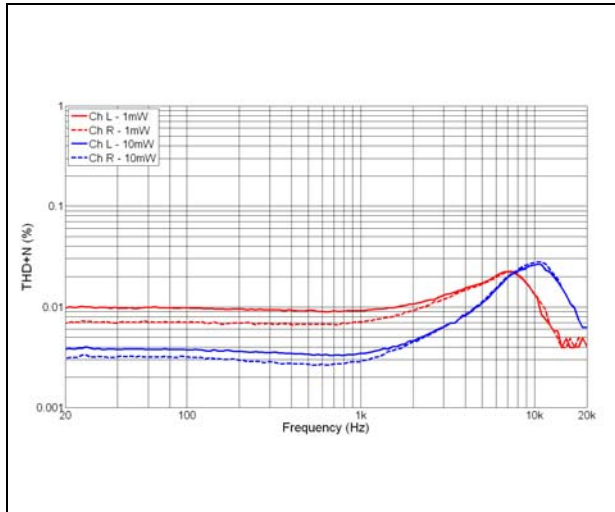


Figure 53. PSRR vs. frequency -  $V_{CC} = 3.6 V$ , gain = 0 dB

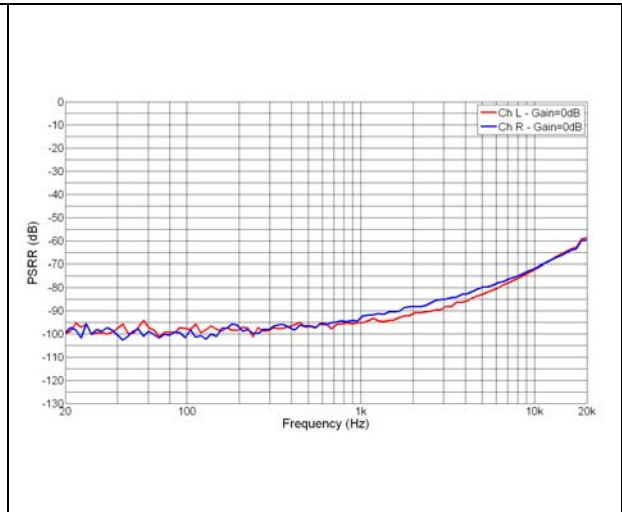


Figure 54. PSRR vs. frequency -  $V_{CC} = 3.6 V$ , gain = +6 dB

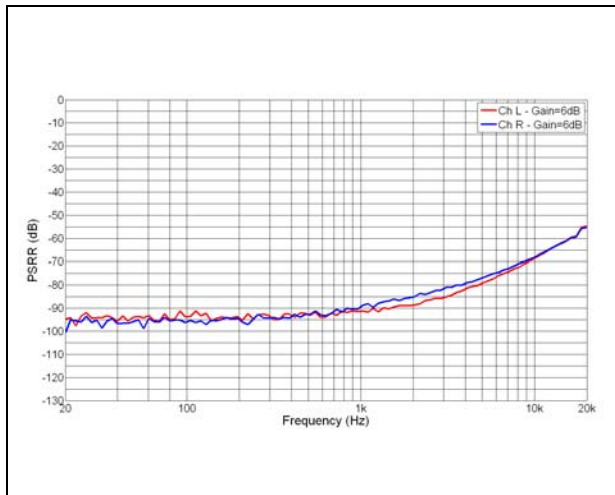


Figure 55. Output signal spectrum ( $V_{CC} = 3.6 V$ , load =  $32 \Omega$ )

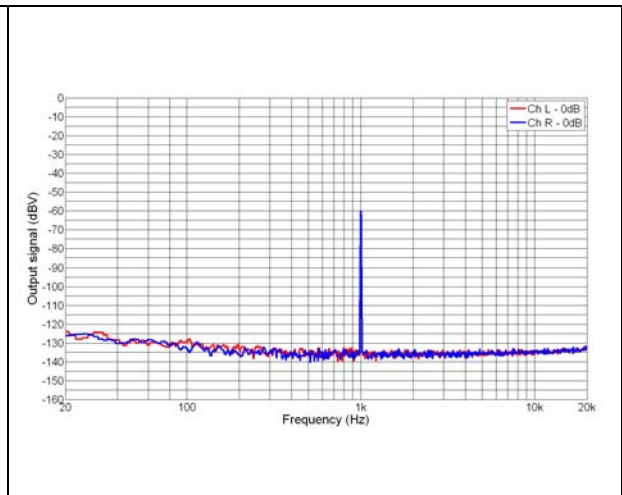




Figure 56. Crosstalk vs. frequency -  $R_L = 32 \Omega$ ,  $V_{CC} = 3.6 V$ , gain = 0 dB

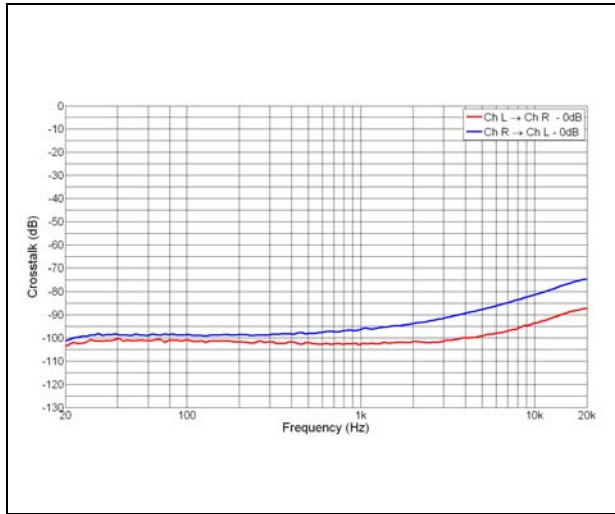


Figure 57. Crosstalk vs. frequency -  $R_L = 32 \Omega$ ,  $V_{CC} = 3.6 V$ , gain = +6 dB

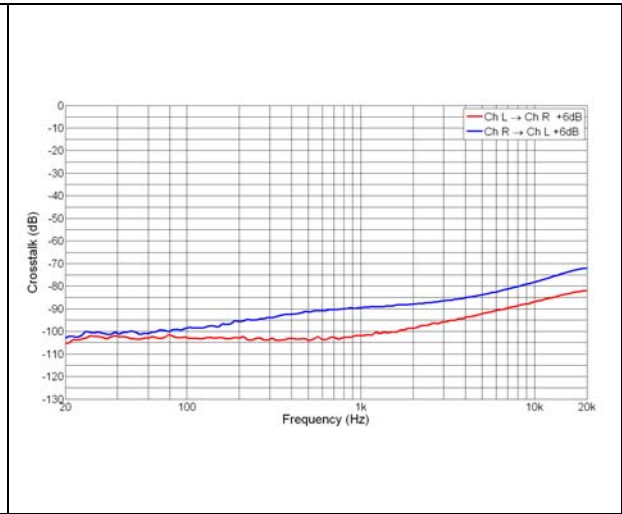


Figure 58. Crosstalk vs. frequency -  $R_L = 47 \Omega$ ,  $V_{CC} = 3.6 V$ , gain = 0 dB

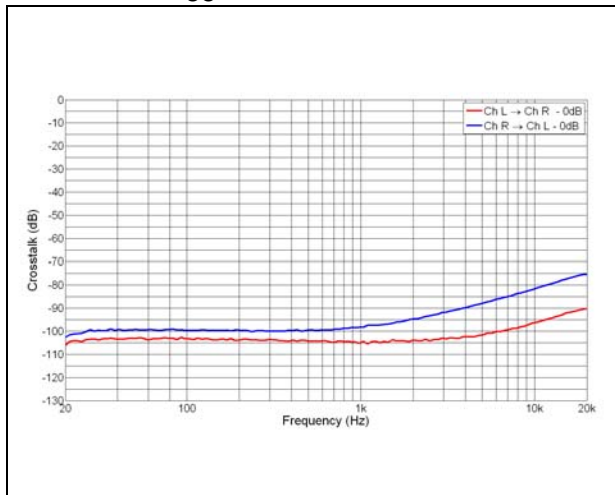


Figure 59. Crosstalk vs. frequency -  $R_L = 47 \Omega$ ,  $V_{CC} = 3.6 V$ , gain = +6 dB

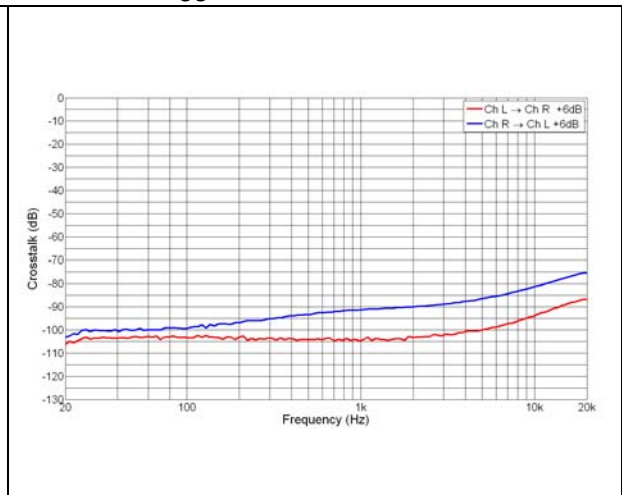


Figure 60. CMRR vs. frequency, 32 Ω, V<sub>CC</sub> = 36 V, 0 dB

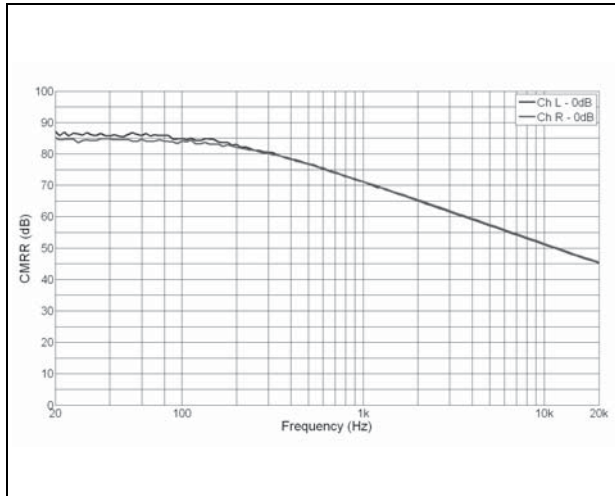


Figure 61. CMRR vs. frequency, 32 Ω, V<sub>CC</sub> = 36 V, 6 dB

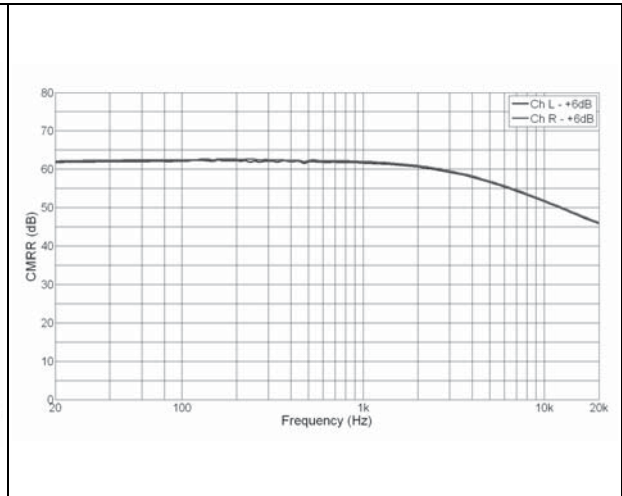


Figure 62. Wake-up time

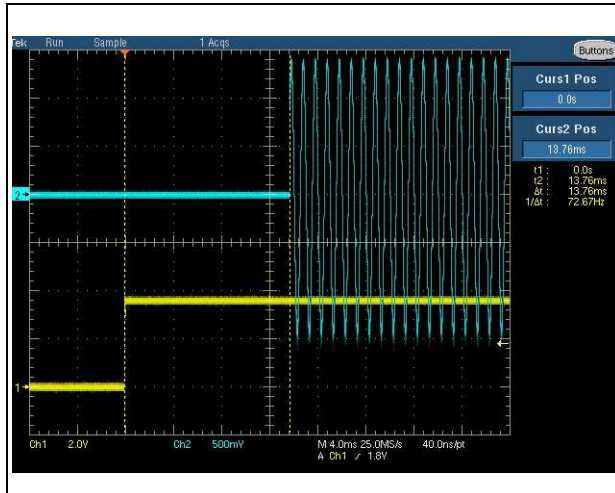
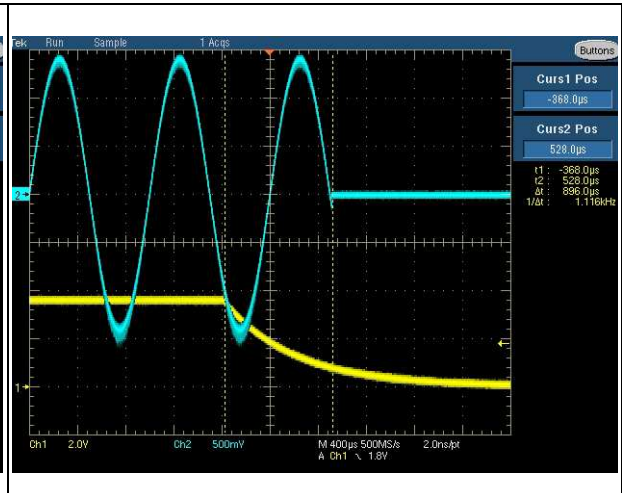


Figure 63. Shutdown



## 4 Application information

### 4.1 Gain control

The A22H165 has two gain settings which are controlled via the GAIN pin:

GAIN voltage	Amplifier gain
$\leq 0.6\text{ V}$	0 dB
$\geq 1.3\text{ V}$	6 dB

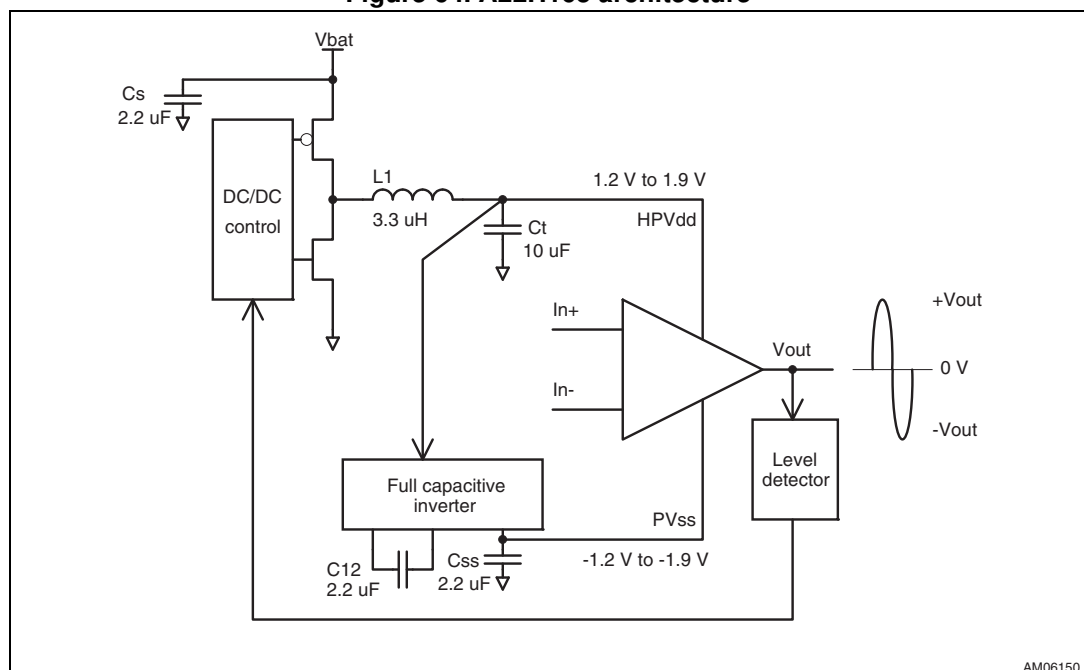
Note: See [Table 6: Electrical characteristics of the amplifier](#) for  $V_{IH}$  and  $V_{IL}$  levels.

### 4.2 Overview of the class-G, 2-level headphone amplifier

The A22H165 uses what is referred to as *class-G operating mode*. This mode is a combination of the class AB biasing technique and an adaptive power supply. For this device, the power supply uses two levels:  $\pm 1.2\text{ V}$  and  $\pm 1.9\text{ V}$ .

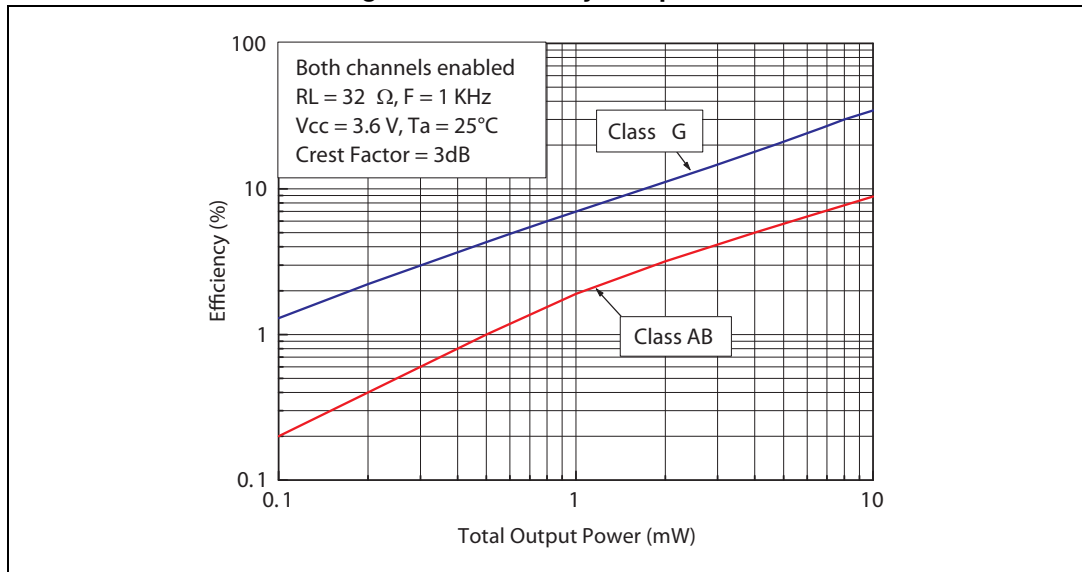
To create the  $\pm 1.2\text{ V}$  and  $\pm 1.9\text{ V}$  levels, the device uses an internal high-efficiency step-down converter linked with a fully capacitive inverter from  $AV_{dd}$ . Thanks to these internally-generated symmetrical power supply voltages, the output of the amplifier can be biased at 0 V, thus eliminating the classical bulky DC blocking output capacitors (typically more than 100  $\mu\text{F}$ ).

Figure 64. A22H165 architecture



When an audio signal is playing with the A22H165, the class G feature adjusts in real time the internal power supply voltage in order to achieve the best efficiency possible. In addition, thanks to the fast transient response of the internal DC-DC converters, the switching between  $\pm 1.2\text{ V}$  and  $\pm 1.9\text{ V}$  can be achieved without audio clipping. Moreover, the out-of-audio band DC-DC switching frequency keeps the audio quality at a high level (distortion, noise, etc...).

Figure 65. Efficiency comparison

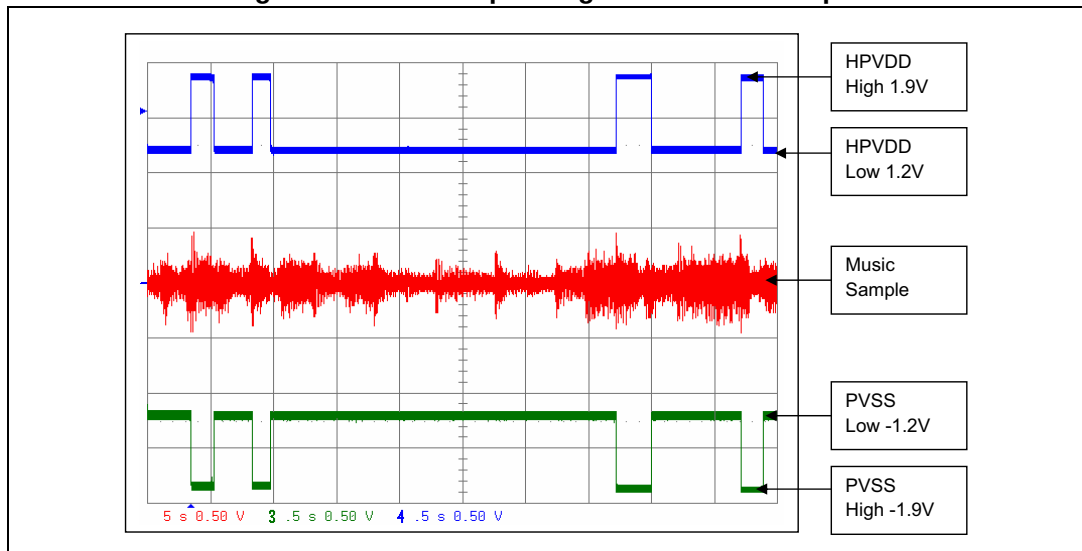


Most audio signals have a crest factor higher than 6 dB (10 dB on average), which means that most of the time the music level is low. In this case, the setting of the internal DC-DC converters is low (1.2 V) and in this way, helps to minimize the power dissipation.

When the audio signal amplitude increases due to a peak or louder music, the setting of the internal DC-DC converters increases to 1.9 V, automatically increasing the output dynamic range. This 1.9 V value remains until the end of the decay time.

Figure 66 shows a music sample played at high levels.

Figure 66. Class-G operating with a music sample



Note: HPVDD/PVSS voltages are created internally by DC-DC converters. To avoid destruction of the A22H165 power amplifier, do not connect any external power supply on these pins.

## 4.3 External component selection

The A22H165 requires few external passive components to operate correctly. Each component is described in the following sections.

### 4.3.1 Step-down inductor selection (L1)

The A22H165 needs one inductor for the internal step-down DC-DC converter. This inductor must fit the following constraints:

- Typical value: 2.2  $\mu\text{H}$  to 3.3  $\mu\text{H}$  (3.3  $\mu\text{H}$  is recommended)
- Maximum current in operating mode: 400 mA
- Minimum inductor value at maximum current: 1.5  $\mu\text{H}$
- Maximum inductor value at zero current: 4.3  $\mu\text{H}$
- DC resistance: from 50 m $\Omega$  up to 450 m $\Omega$

[Table 7](#) shows the part number that should be used according to the inductor value.

**Table 7. Recommended inductor**

Manufacturer	Part number	Value
Murata	LQM21PN3R3NGRD	3.3 $\mu\text{H}$
	LQM2MPN3R3G0L	3.3 $\mu\text{H}$
	LQM2MPN2R2G0L	2.2 $\mu\text{H}$
FDK	MIPSZ2012D3R3	3.3 $\mu\text{H}$
	MIPSZ2012D2R2	2.2 $\mu\text{H}$

### 4.3.2 Step-down output capacitor selection (C<sub>T</sub>)

For the internal DC-DC step-down converter, the A22H165 needs one output capacitor.

The three criteria for selecting the output capacitor are the range value of the capacitor including self tolerance, DC variation and the minimum ESR value, which is mandatory to avoid oscillation of the converter. Therefore the following constraints must be observed.

- Typical capacitor value: 10  $\mu\text{F}$  at DC = 0 V
- Maximum capacitor value: 12  $\mu\text{F}$  at DC = 0 V
- Minimum capacitor value: 4.8  $\mu\text{F}$  at DC = 2 V
- Voltage range across this capacitor: from 1.1 V to 2 V
- Minimum DC ESR value: 5 m $\Omega$

A ceramic capacitor in a 0603-type package is also recommended because of its close placement to the A22H165, which makes it easier to minimize parasitic inductance and resistance that have a negative impact on the audio performance.

**Table 8. Recommended capacitors**

Manufacturer	Part number	Value
Murata	GRM188R60J106ME47	10 $\mu\text{F}$ , 6.3 V, X5R
	GRM188R60J106ME84	10 $\mu\text{F}$ , 6.3 V, X5R
	GRM188R61E106ME73	10 $\mu\text{F}$ , 25 V, X5R

### 4.3.3 Full capacitive inverter capacitors selection (C12 and C<sub>SS</sub>)

Two capacitors (C12 and C<sub>SS</sub>) are needed for this internal DC-DC inverter.

The three criteria for selecting these capacitors are the range value of the capacitor including self tolerance, DC variation and the minimum ESR to minimize power losses.

- Typical capacitor value: 2.2 μF +/-20 %
- Voltage across these capacitors: from 1.1 V to 2 V
- Minimum capacitor value: 1 μF

Again, a ceramic capacitor in a 0603 or 0402-type package is also recommended because of their close placement to the A22H165, which makes it easier to minimize parasitic inductance and resistance that have a negative impact on the audio performance.

### 4.3.4 Power supply decoupling capacitor selection (Cs)

A 2.2 μF decoupling capacitor with low ESR is recommended for positive power supply decoupling. Packages such as the 0402 or 0603 are also recommended because of their close placement to the A22H165, which makes it easier to minimize parasitic inductance. It is advised to choose a X5R dielectric for capacitor tolerance, and a 10 V DC rating voltage for 4.8 V operations (or a 6.3 V DC rating voltage for 3.6 V operations), to take into consideration the ΔC/ΔV variation of this type of ceramic capacitor.

An important parameter is the rated voltage of the capacitor. A 2.2 μF/6.3 V capacitor used at 4.8 V DC typically loses about 40 % of its value. In fact, with a 4.8 V power supply voltage, the decoupling value is about 1.3 μF instead of 2.2 μF. Because the decoupling capacitor influences the THD+N in the medium-to-high frequency region, this capacitor variation becomes decisive. In addition, less decoupling means higher overshoots, which can be problematic if they reach the power supply's AMR value (5.5 V). This is why, for a 2.2 μF value, we recommend a 2.2 μF/10 V, a 4.7 μF/6.3 V or a ceramic capacitor with a low DC bias variation rated at 6.3 V.

### 4.3.5 Input coupling capacitor selection (C<sub>in</sub>)

C<sub>in</sub> input coupling capacitors are mandatory for the A22H165's operation. They block any DC component coming from the audio signal source.

C<sub>in</sub> with R<sub>in</sub> form a first-order high-pass filter and the -3 dB cut-off frequency is:

$$FC(-3dB) = \frac{1}{2 \times \pi \times R_{in} \times C_{in}}$$

R<sub>in</sub> is the single-ended input impedance that can be approximated at about R<sub>indiff</sub>/2.

R<sub>in</sub> also depends on the gain setting. [Figure 10](#) provides the differential input impedance vs. gain. One can also see that R<sub>indiff</sub> is minimum for the maximum gain setting (that is, 6 dB). Therefore, in most cases, R<sub>in</sub> should be set to 6 dB to calculate the minimum input capacitor C<sub>in</sub>.

Example:

In this case and for a -3 dB cut-off frequency of 20 Hz, C<sub>in</sub> = 0.64 μF. The closest normalized value is 0.68 μF but a 1 μF capacitor is more suitable to take into consideration the capacitor tolerance +/-20 %.

If the aim is to have the 20 Hz at -1 dB, the capacitor has to be multiplied by 1.96. As such, C<sub>in</sub> = 0.64 x 1.96 = 1.25 μF. The closest normalized value would be 1.5 μF or 2.2 μF.